

NSR05T30P2

500 mA, 30 V Schottky Barrier Diode

These Schottky barrier diodes are optimized for low forward voltage drop and low leakage current that offers the most optimal power dissipation in applications. They are housed in spacing saving micro-packaging ideal for space constraint applications.

Features

- Low Forward Voltage Drop – 450 mV (Typ.) @ $I_F = 500$ mA
- Low Reverse Current – 40 μ A (Typ.) @ $V_R = 30$ V
- 500 mA of Continuous Forward Current
- ESD Rating: – Human Body Model: Class 3B
– Charged Device Model: Class IV
- High Switching Speed
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

- LCD and Keypad Backlighting
- Camera Photo Flash
- Buck and Boost dc-dc Converters
- Reverse Voltage and Current Protection
- Clamping & Protection

MAXIMUM RATINGS

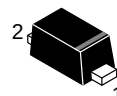
Rating	Symbol	Value	Unit
Reverse Voltage	V_R	30	V
Forward Current (DC)	I_F	500	mA
Forward Surge Current (60 Hz @ 1 cycle)	I_{FSM}	2.5	A
Repetitive Peak Forward Current (Pulse Wave = 1 sec, Duty Cycle = 66%)	I_{FRM}	1	A
ESD Rating: Human Body Model Charged Device Model	ESD	> 8 > 1	kV

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



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SOD-923
CASE 514AB

MARKING DIAGRAM



YN = Specific Device Code
M = Date Code



ORDERING INFORMATION

Device	Package	Shipping†
NSR05T30P2T5G	SOD-923 (Pb-Free)	2 mm Pitch 8000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NSR05T30P2

THERMAL CHARACTERISTICS

Characteristic	Symbol	Min	Typ	Max	Unit
Thermal Resistance Junction-to-Ambient (Note 1) Total Power Dissipation @ $T_A = 25^\circ\text{C}$	$R_{\theta JA}$ P_D			345 360	$^\circ\text{C/W}$ mW
Thermal Resistance Junction-to-Ambient (Note 2) Total Power Dissipation @ $T_A = 25^\circ\text{C}$	$R_{\theta JA}$ P_D			175 715	$^\circ\text{C/W}$ mW
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150			$^\circ\text{C}$

1. Mounted onto a 4 in square FR-4 board 50 mm sq. 1 oz. Cu 0.06" thick single sided. Operating to steady state.
2. Mounted onto a 4 in square FR-4 board 650 mm sq. 1 oz. Cu 0.06" thick single sided. Operating to steady state.

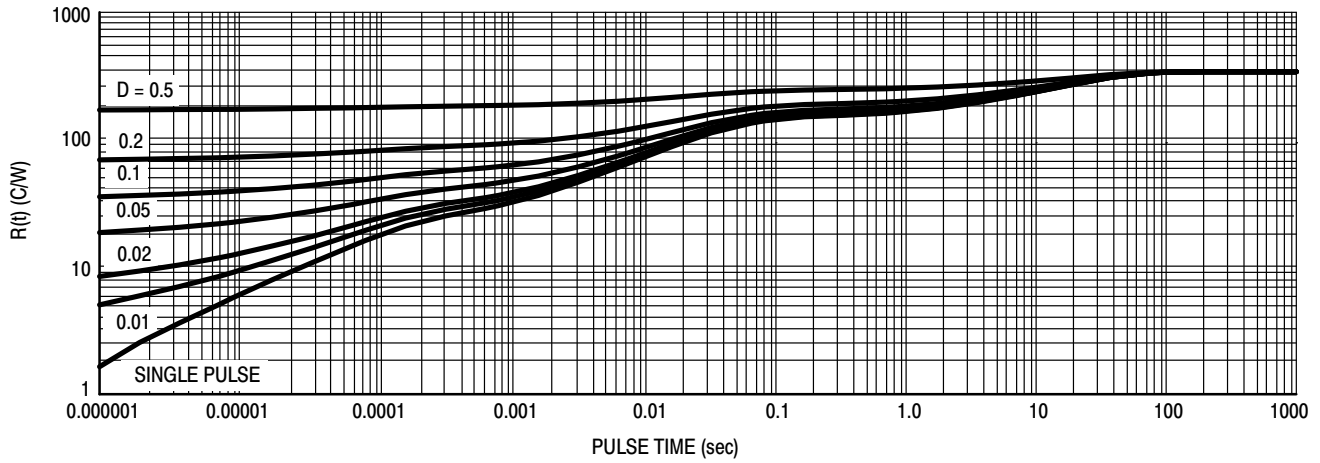


Figure 1. Thermal Response (Note 1)

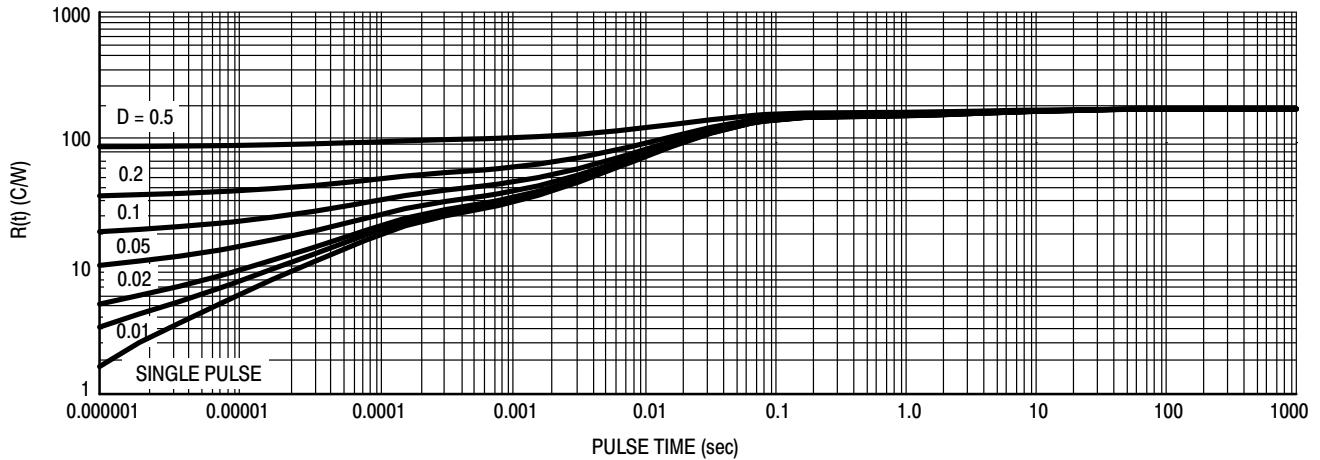


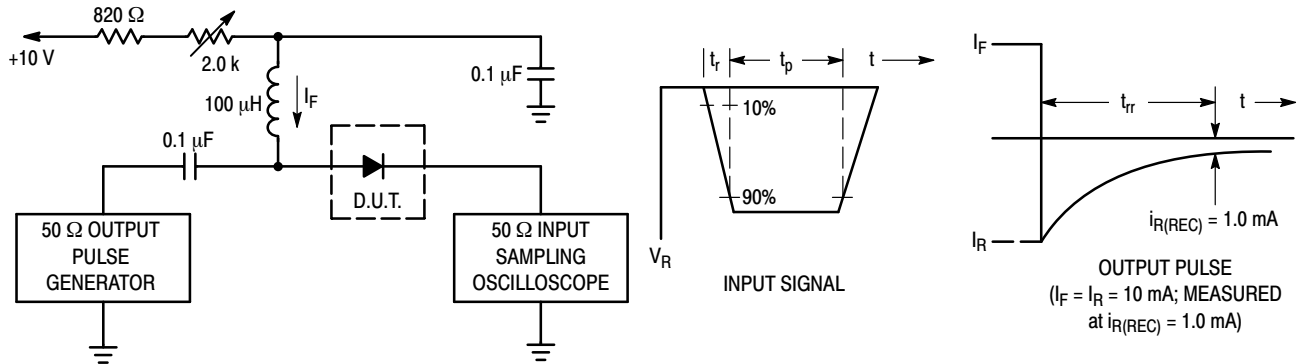
Figure 2. Thermal Response (Note 2)

NSR05T30P2

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
Reverse Leakage ($V_R = 10\text{ V}$) ($V_R = 30\text{ V}$)	I_R		15 40	26 85	μA
Forward Voltage ($I_F = 10\text{ mA}$) ($I_F = 100\text{ mA}$) ($I_F = 200\text{ mA}$) ($I_F = 500\text{ mA}$)	V_F		225 310 350 450	255 335 385 485	mV
Total Capacitance ($V_R = 1.0\text{ V}$, $f = 1.0\text{ MHz}$)	C_T		33		pF
Reverse Recovery Time ($I_F = I_R = 10\text{ mA}$, $I_{R(\text{REC})} = 1.0\text{ mA}$, Figure 3)	t_{rr}		9		ns
Peak Forward Recovery Voltage ($I_F = 100\text{ mA}$, $t_r = 20\text{ ns}$, Figure 4)	V_{FRM}		460		mV

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.



- Notes: 1. A 2.0 k Ω variable resistor adjusted for a Forward Current (I_F) of 10 mA.
2. Input pulse is adjusted so $I_{R(\text{peak})}$ is equal to 10 mA.
3. $t_p \gg t_{rr}$

Figure 3. Recovery Time Equivalent Test Circuit

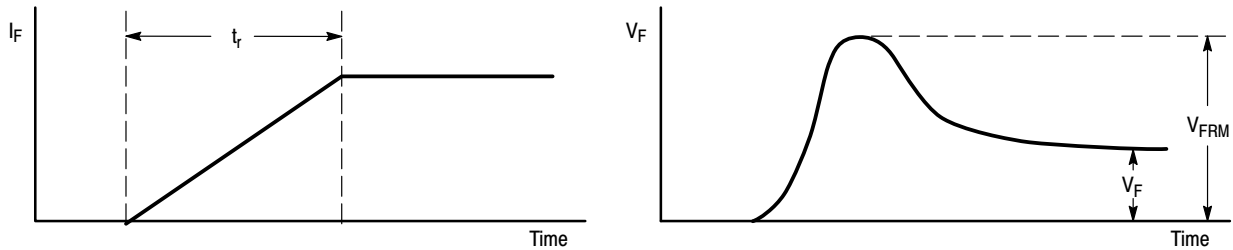


Figure 4. Peak Forward Recovery Voltage Definition

TYPICAL CHARACTERISTICS

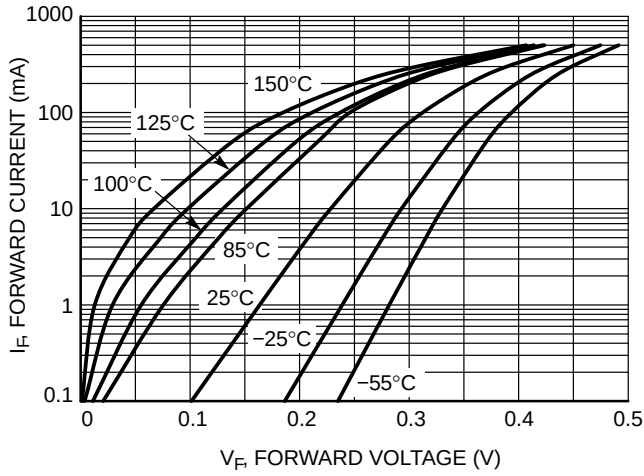


Figure 5. Forward Voltage

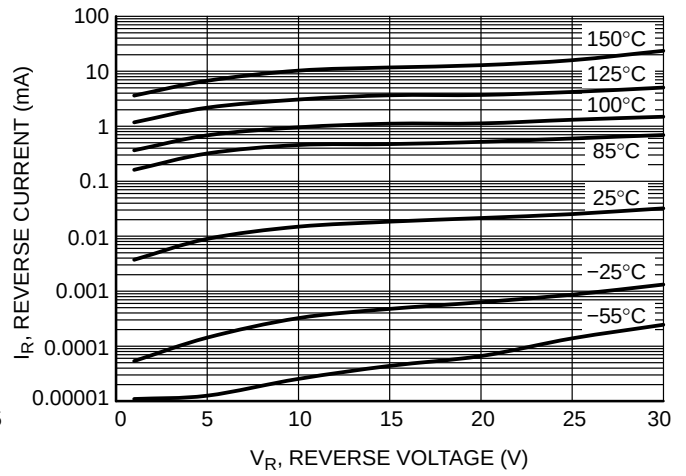


Figure 6. Leakage Current

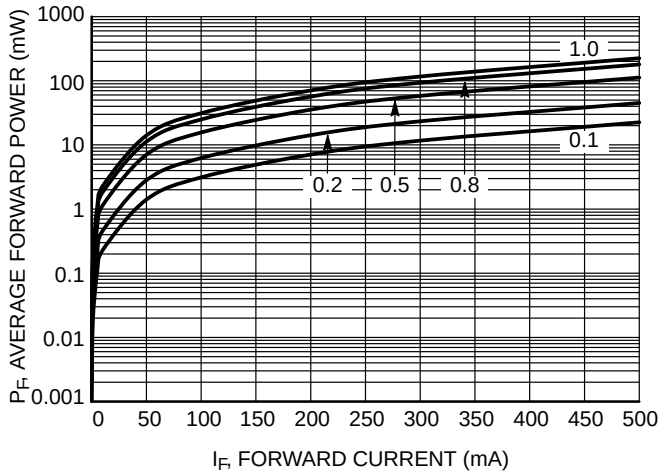


Figure 7. Average Forward Power Dissipation

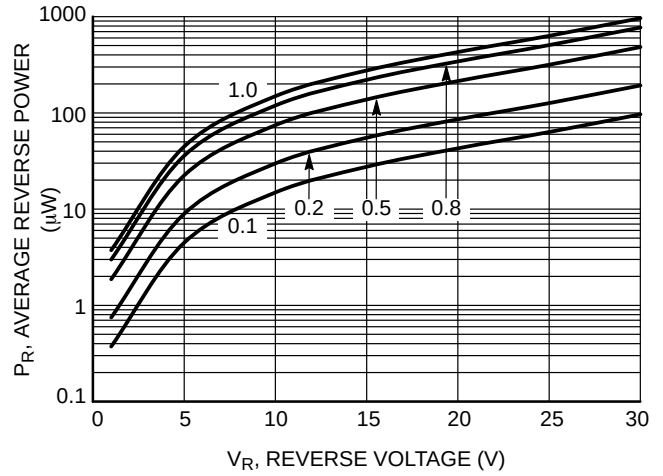


Figure 8. Average Reverse Power Dissipation

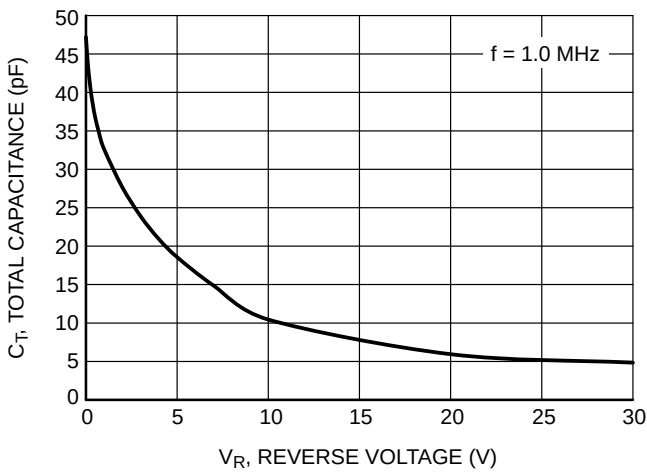


Figure 9. Total Capacitance

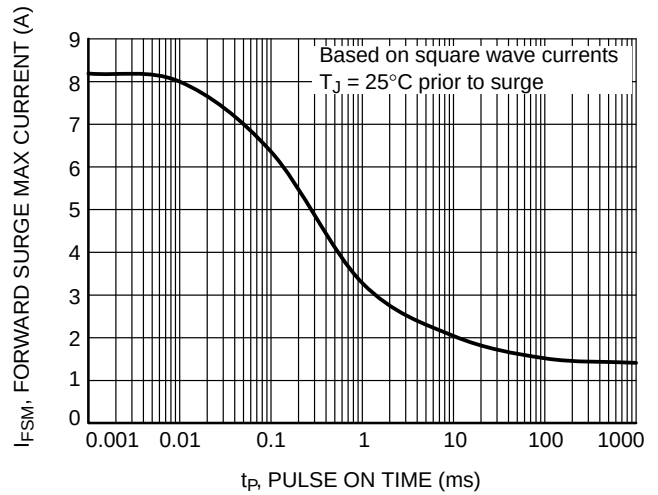
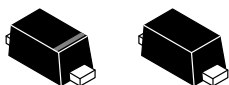


Figure 10. Forward Surge Current

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

ON Semiconductor®

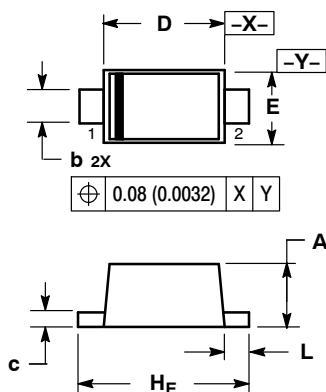


STYLE 1 STYLE 2

SCALE 8:1

SOD-923
CASE 514AB-01
ISSUE B

DATE 07 MAR 2007

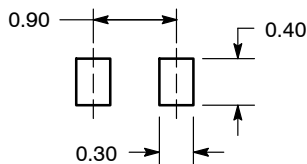


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.34	0.37	0.40	0.013	0.015	0.016
b	0.15	0.20	0.25	0.006	0.008	0.010
c	0.07	0.12	0.17	0.003	0.005	0.007
D	0.75	0.80	0.85	0.030	0.031	0.033
E	0.55	0.60	0.65	0.022	0.024	0.026
H _E	0.95	1.00	1.05	0.037	0.039	0.041
L	0.05	0.10	0.15	0.002	0.004	0.006

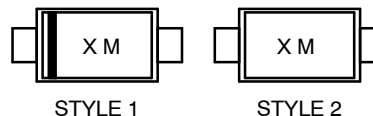
SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



X = Specific Device Code
M = Date Code

*This information is generic. Please refer to device data sheet for actual part marking.
Pb-Free indicator, "G" or microdot "▪", may or may not be present.

STYLE 1:
PIN 1. CATHODE (POLARITY BAND)
2. ANODE

STYLE 2:
NO POLARITY

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DESCRIPTION:	SOD-923, 1.0X0.6X0.37, MAX HEIGHT 0.40	PAGE 1 OF 1

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